

# VHF POWER MOSFET

## N-Channel Enhancement Mode

**DESCRIPTION:**

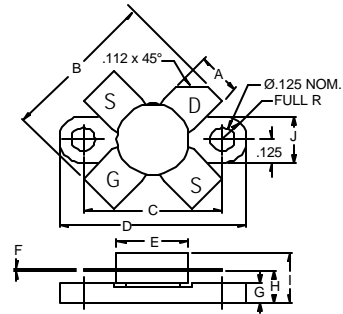
The **VFT15-28** is Designed for General Purpose Class B Power Amplifier Applications up to 175 MHz.

**FEATURES:**

- $P_G = 14$  dB Typ. at 15 W /175MHz
- 10:1 Load VSWR Capability
- *Omnigold*<sup>TM</sup> Metalization System

**MAXIMUM RATINGS**

$I_D$	2.5 A
$V_{(BR)DSS}$	65 V
$V_{DGR}$	65 V
$V_{GS}$	$\pm 40$ V
$P_{DISS}$	55 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$q_{JC}$	$3.2^\circ C/W$

**PACKAGE STYLE .380 4L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

**ORDER CODE: ASI10702**
**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_{DS} = 5.0$ mA		60	---	---	V
$I_{DSS}$	$V_{DS} = 28$ V	$V_{GS} = 0$ V		---	---	2.0	mA
$I_{GSS}$	$V_{DS} = 0$ V	$V_{GS} = 40$ V		---	---	1.0	mA
$V_{GS}$	$V_{DS} = 10$ V	$I_D = 25$ mA		1.0	---	6.0	V
$G_{FS}$	$V_{DS} = 10$ V	$I_D = 250$ mA		250	---	---	mS
$C_{iss}$	$V_{GS} = 28$ V	$V_{DS} = 0$ V	$F = 1.0$ MHz		22		pF
$C_{oss}$					17		
$C_{rss}$					3.0		
$P_G$	$V_{DD} = 28$ V	$I_{DQ} = 25$ mA	$P_{OUT} = 15$ W	13	14		dB
$h_D$	$F = 175$ MHz			50	60		%



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*ADVANCED SEMICONDUCTOR, INC.*

7525 ETHEL AVENUE • NORTH HOLLYWOOD, CA 91605 • (818) 982-1202 • TELEX: 18-2651 • FAX (818) 765-3004